

ABSTRACT OF THE DISCLOSURE

It is disclosed an over-coating agent for forming fine-line patterns which is applied to cover a substrate having thereon photoresist patterns and allowed to shrink under heat so that the spacing between adjacent photoresist patterns is lessened, with the applied film of the over-coating agent being removed substantially completely to form or define fine trace patterns, further characterized by containing a copolymer or a mixture of polyvinyl alcohol with a water-soluble polymer other than polyvinyl alcohol. Also disclosed is a method of forming fine-line patterns using the over-coating agent. According to the invention, one can effectively increase the shrinkage amount (the amount of heat shrinking) of the agent, thereby achieving a remarkably improved effect of forming or defining fine-line patterns and which also present satisfactory profiles and meet the characteristics required of today's semiconductor devices.